

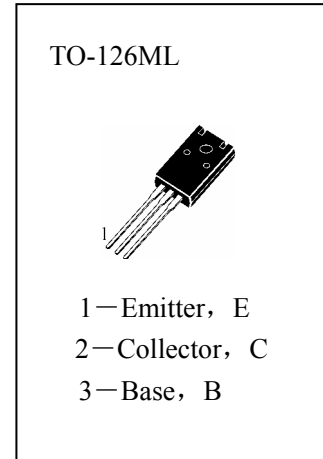
H1144

APPLICATIONS

Medium frequency power amplifier, Medium Seed switching.

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	—Storage Temperature	-55~150°C
T _j	—Junction Temperature	150°C
P _C	—Collector Dissipation (T _c =25°C)	10W
P _C	—Collector Dissipation (T _A =25°C)	1.5W
V _{CBO}	—Collector-Base Voltage	-120V
V _{CEO}	—Collector-Emitter Voltage	-100V
V _{EBO}	—Emitter-Base Voltage	-6V
I _C	—Collector Current	-1.5A



ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CBO}	Collector-Base Breakdown Voltage	-120			V	I _C =-10 μA, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	-100			V	I _C =-1mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	-6			V	I _E =-10 μA, I _C =0
I _{CBO}	Collector Cut-off Current			-100	nA	V _{CB} =-100V, I _E =0
I _{EBO}	Emitter Cut-off Current			-100	nA	V _{EB} =-4V, I _C =0
H _{FE} (1)	DC Current Gain	100		400		V _{CE} =-5V, I _C =-100mA
H _{FE} (2)	DC Current Gain	30				V _{CE} =-5V, I _C =-1A
V _{CE(sat)}	Collector- Emitter Saturation Voltage		0.18	0.5	V	I _C =-500mA, I _B =-50mA
V _{BE(sat)}	Base-Emitter Saturation Voltage		0.85	1.2	V	I _C =-500mA, I _B =-50mA
t _{ON}	Turn-On Time		80		nS	} See specified test circuit
t _{STG}	Storage Time		750		nS	
t _F	Fall Time		40		nS	
f _t	Current Gain-Bandwidth Product		100		MHz	V _{CE} =-10V, I _C =-50mA,
C _{ob}	Output Capacitance		18		pF	V _{CB} =-10V, I _E =0, f=1MHz

h_{FE} Classification

R	S	T
100—200	140—280	200—400